



MAR 12 2004

TRANSMITTAL OF FORMAL DRAWINGS

Docket No.
YOR920030137US1 (16602)

Application Of: Stephen W. Bedell, et al.

Serial No.	Filing Date	Confirmation No.	Examiner	Art Unit
10/654,231	9/3/2003	4747	S. Mulpuri	2812

Invention: METHOD OF MEASURING CRYSTAL DEFECTS IN THIN Si/SiGe BILAYERS

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

2 sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).

Signature

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Dated: March 10, 2004

I certify that this document and attached formal drawings
are being deposited on 3/10/2004 with the
U.S. Postal Service as first class mail under 37 C.F.R. 1.8
and addressed to the Commissioner for Patents, P.O. Box
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Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D.

Typed or Printed Name of Person Mailing Correspondence